

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



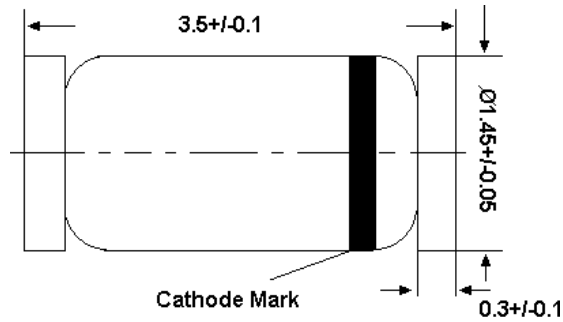
PLED

BZV55C2V0-MS THRU BZV55C75-MS

Product specification

Silicon Epitaxial Planar Zener Diodes

in MiniMELF case especially for automatic insertion. The Zener voltages are graded according to the international E24 standard. Smaller voltage tolerances and higher Zener voltages are upon request.



Glass case MiniMELF
Dimensions in mm

REEL SPECIFICATION

P/N	PKG	QTY
BZV55C2V0-MS THRU BZV55C75-MS	LL34	2500

Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Value	Unit
Power Dissipation	P _{tot}	500 ¹⁾	mW
Junction Temperature	T _j	175	°C
Storage Temperature Range	T _{stg}	- 55 to + 175	°C
¹⁾ Valid provided that electrodes are kept at ambient temperature			

Characteristics at Ta = 25°C

Thermal Resistance Junction to Ambient Air	R _{thA}	0.3 ¹⁾	K/mW
Forward Voltage at I _F = 100 mA	V _F	1	V
¹⁾ Valid provided that electrodes are kept at ambient temperature			

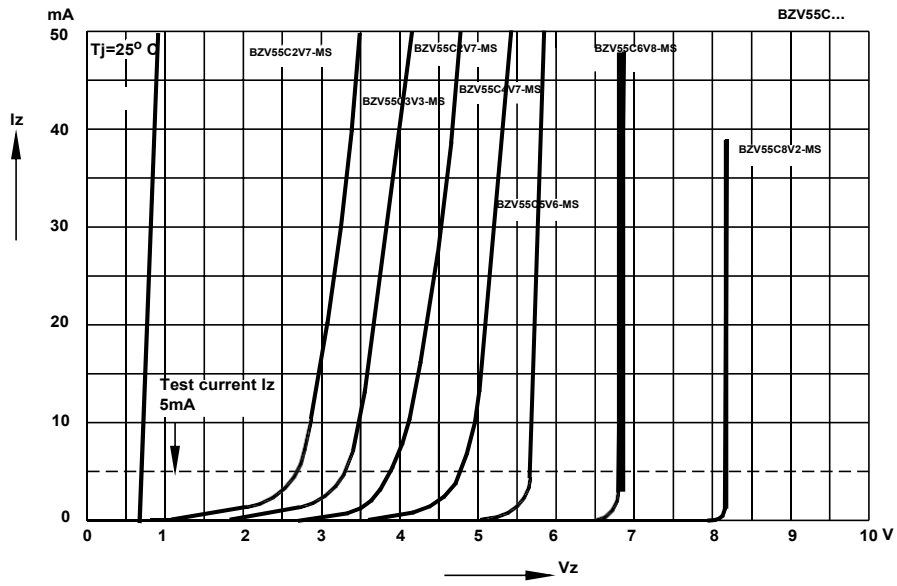
Characteristics at Ta = 25°C

P/N	Zener Voltage Range ¹⁾			Dynamic Resistance			Reverse Leakage Current			Temp. Coefficient of Zener Voltage
	V _{Zno} _m	V _{ZT}	at I _{ZT}	Z _{ZT}	Z _{ZK}	at I _{ZK}	T _a = 25°C	T _a = 125°C	at V _R	
	(V)	(V)	(mA)	Max. (Ω)	Max. (Ω)	(mA)	Max. (μA)	Max. (μA)	(V)	TKvz (%/K)
BZV55C2V0-MS	2.0	1.8...2.15	5	85	600	1	100	200	1	-0.09...-0.06
BZV55C2V2-MS	2.2	2.08...2.33	5	85	600	1	75	160	1	-0.09...-0.06
BZV55C2V4-MS	2.4	2.28...2.56	5	85	600	1	50	100	1	-0.09...-0.06
BZV55C2V7-MS	2.7	2.5...2.9	5	85	600	1	10	50	1	-0.09...-0.06
BZV55C3V0-MS	3.0	2.8...3.2	5	85	600	1	4	40	1	-0.08...-0.05
BZV55C3V3-MS	3.3	3.1...3.5	5	85	600	1	2	40	1	-0.08...-0.05
BZV55C3V6-MS	3.6	3.4...3.8	5	85	600	1	2	40	1	-0.08...-0.05
BZV55C3V9-MS	3.9	3.7...4.1	5	85	600	1	2	40	1	-0.08...-0.05
BZV55C4V3-MS	4.3	4...4.6	5	75	600	1	1	20	1	-0.06...-0.03
BZV55C4V7-MS	4.7	4.4...5	5	60	600	1	0.5	10	1	-0.05...+0.02
BZV55C5V1-MS	5.1	4.8...5.4	5	35	550	1	0.1	2	1	-0.02...+0.02
BZV55C5V6-MS	5.6	5.2...6	5	25	450	1	0.1	2	1	-0.05...+0.05
BZV55C6V2-MS	6.2	5.8...6.6	5	10	200	1	0.1	2	2	0.03...0.06
BZV55C6V8-MS	6.8	6.4...7.2	5	8	150	1	0.1	2	3	0.03...0.07
BZV55C7V5-MS	7.5	7...7.9	5	7	50	1	0.1	2	5	0.03...0.07
BZV55C8V2-MS	8.2	7.7...8.7	5	7	50	1	0.1	2	6.2	0.03...0.08
BZV55C9V1-MS	9.1	8.5...9.6	5	10	50	1	0.1	2	6.8	0.03...0.09
BZV55C10-MS	10	9.4...10.6	5	15	70	1	0.1	2	7.5	0.03...0.1
BZV55C11-MS	11	10.4...11.6	5	20	70	1	0.1	2	8.2	0.03...0.11
BZV55C12-MS	12	11.4...12.7	5	20	90	1	0.1	2	9.1	0.03...0.11
BZV55C13-MS	13	12.4...14.1	5	26	110	1	0.1	2	10	0.03...0.11
BZV55C15-MS	15	13.8...15.6	5	30	110	1	0.1	2	11	0.03...0.11
BZV55C16-MS	16	15.3...17.1	5	40	170	1	0.1	2	12	0.03...0.11
BZV55C18-MS	18	16.8...19.1	5	50	170	1	0.1	2	13	0.03...0.11
BZV55C20-MS	20	18.8...21.2	5	55	220	1	0.1	2	15	0.03...0.11
BZV55C22-MS	22	20.8...23.3	5	55	220	1	0.1	2	16	0.04...0.12
BZV55C24-MS	24	22.8...25.6	5	80	220	1	0.1	2	18	0.04...0.12
BZV55C27-MS	27	25.1...28.9	5	80	220	1	0.1	2	20	0.04...0.12
BZV55C30-MS	30	28...32	5	80	220	1	0.1	2	22	0.04...0.12
BZV55C33-MS	33	31...35	5	80	220	1	0.1	2	24	0.04...0.12
BZV55C36-MS	36	34...38	5	80	220	1	0.1	2	27	0.04...0.12
BZV55C39-MS	39	37...41	2.5	90	500	0.5	0.1	5	30	0.04...0.12
BZV55C43-MS	43	40...46	2.5	90	500	0.5	0.1	5	33	0.04...0.12
BZV55C47-MS	47	44...50	2.5	110	600	0.5	0.1	5	36	0.04...0.12
BZV55C51-MS	51	48...54	2.5	125	700	0.5	0.1	10	39	0.04...0.12
BZV55C56-MS	56	52...60	2.5	135	700	0.5	0.1	10	43	0.04...0.12
BZV55C62-MS	62	58...66	2.5	150	1000	0.5	0.1	10	47	0.04...0.12
BZV55C68-MS	68	64...72	2.5	200	1000	0.5	0.1	10	51	0.04...0.12
BZV55C75-MS	75	70...79	2.5	250	1000	0.5	0.1	10	56	0.04...0.12

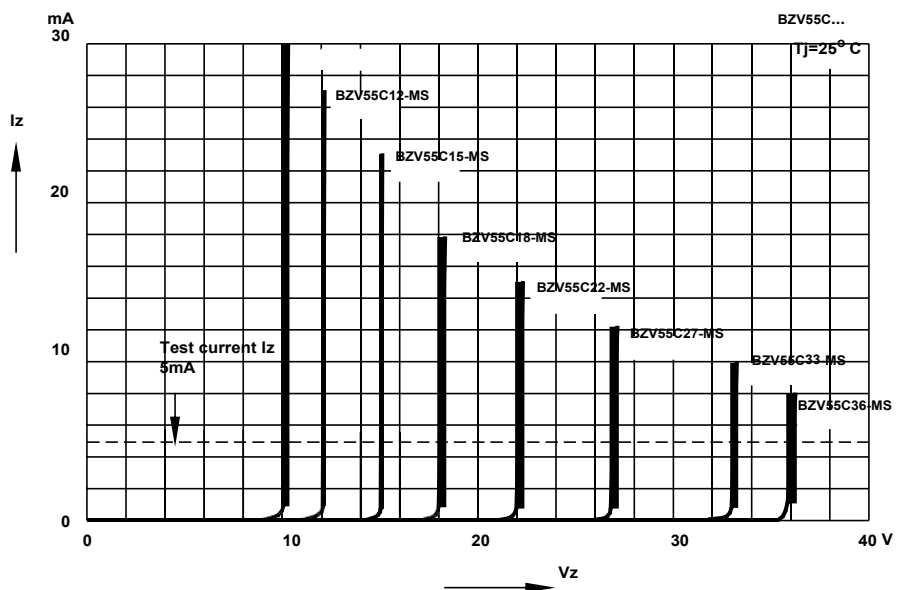
1) Tested with pulses t_p = 20 ms.

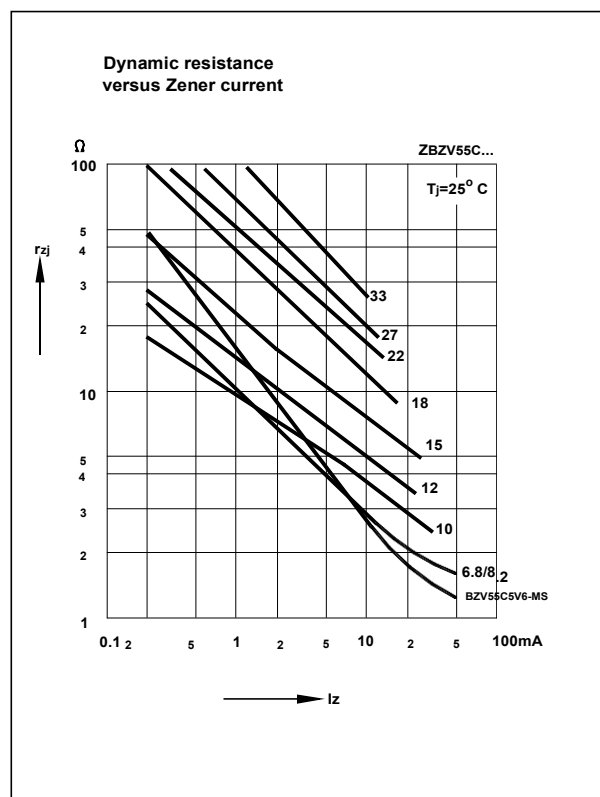
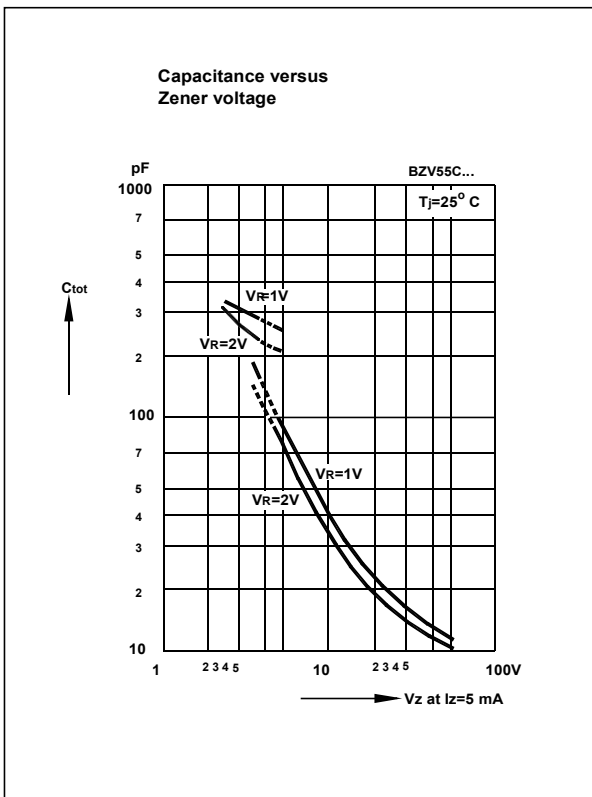
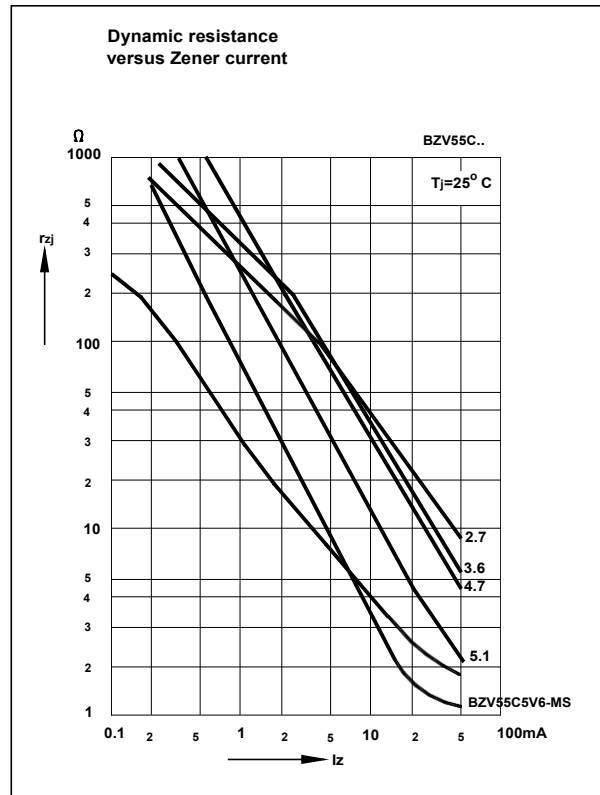
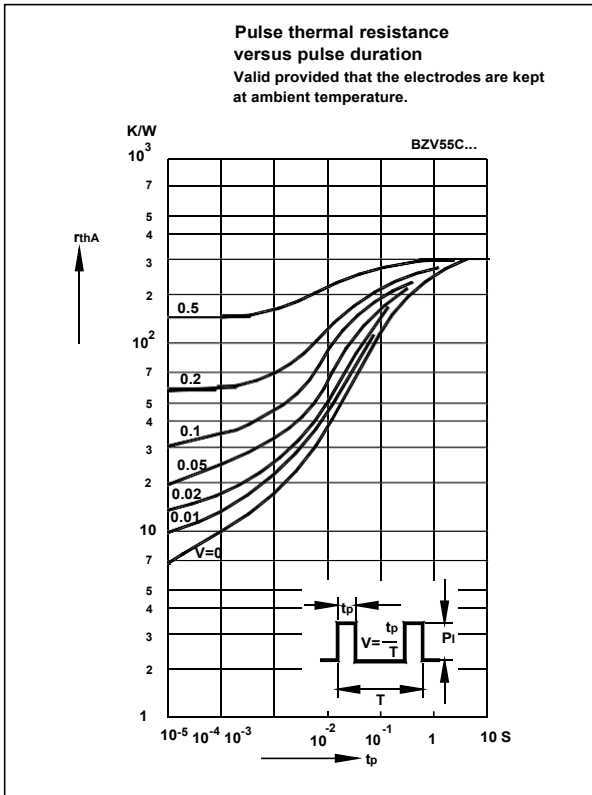
2) The BZV55C is a silicon diode with operation in forward direction. Hence, the index of all parameters should be "F" instead of "Z". Connect the cathode electrode to the negative pole.

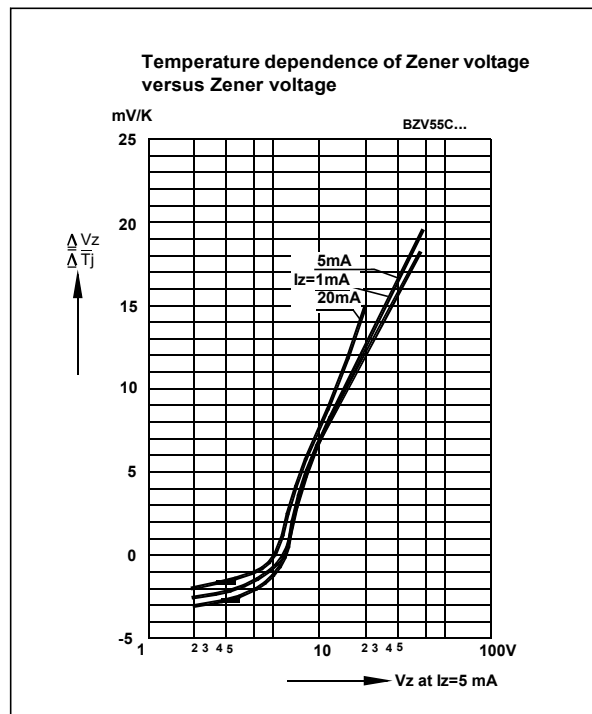
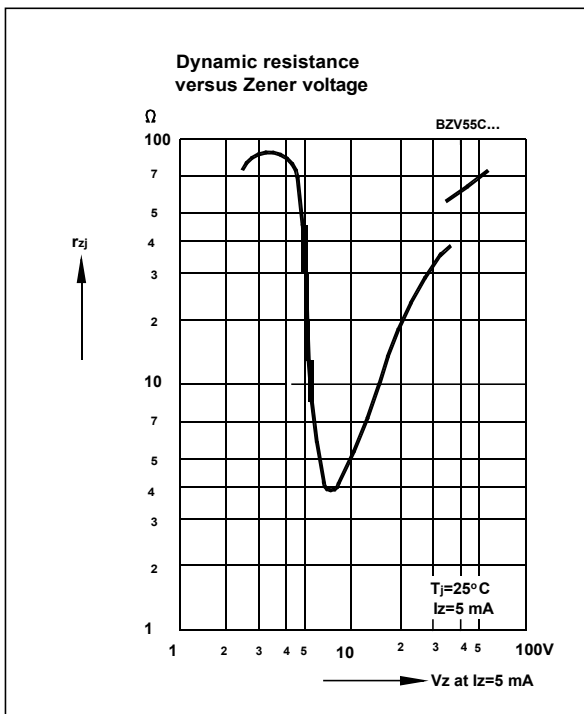
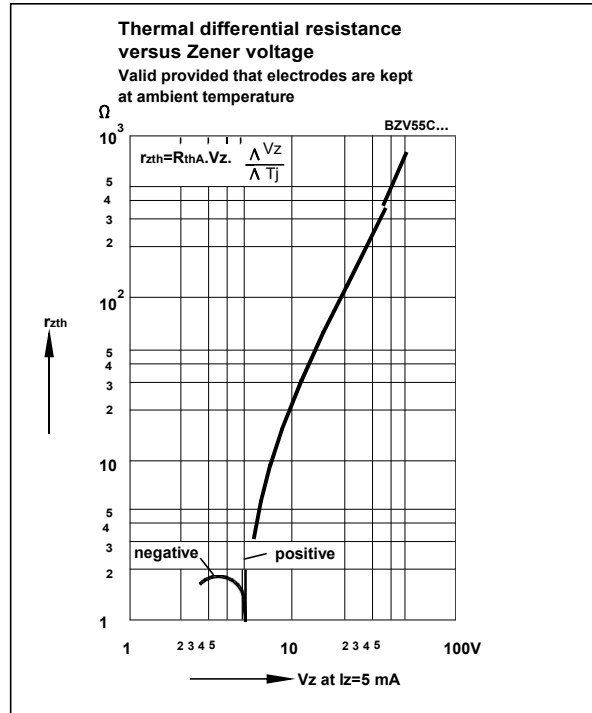
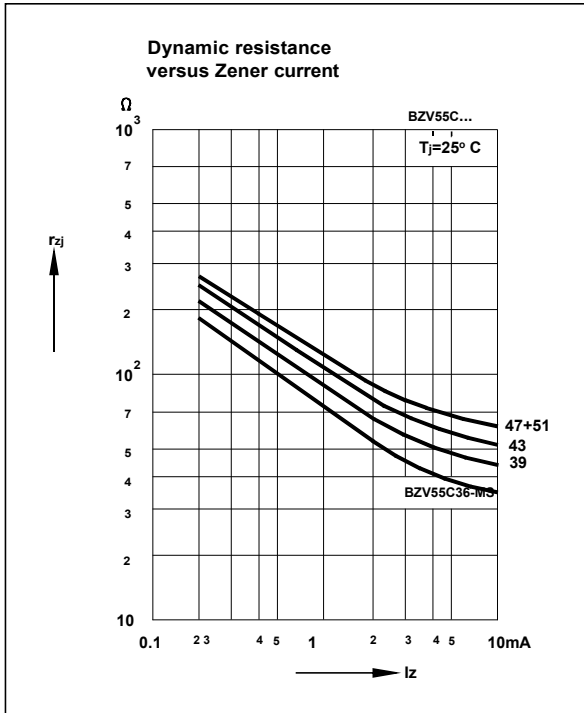
Breakdown characteristics
T_j = constant (pulsed)

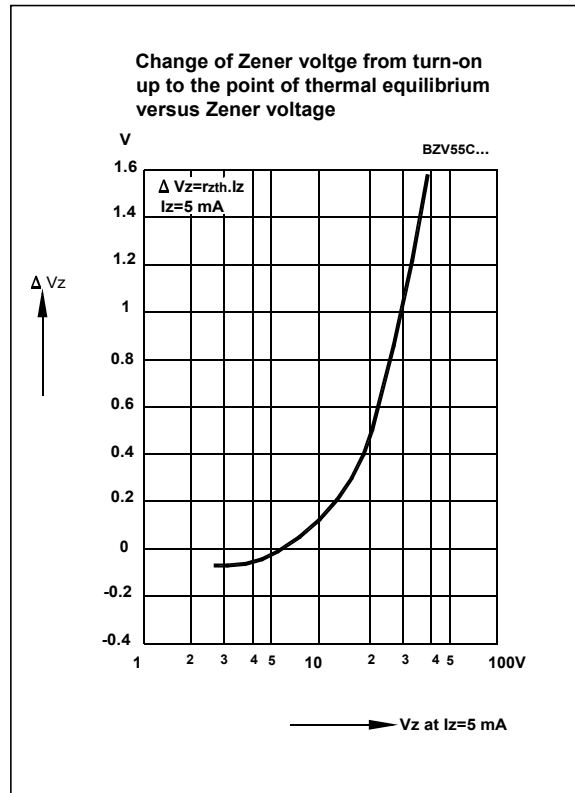
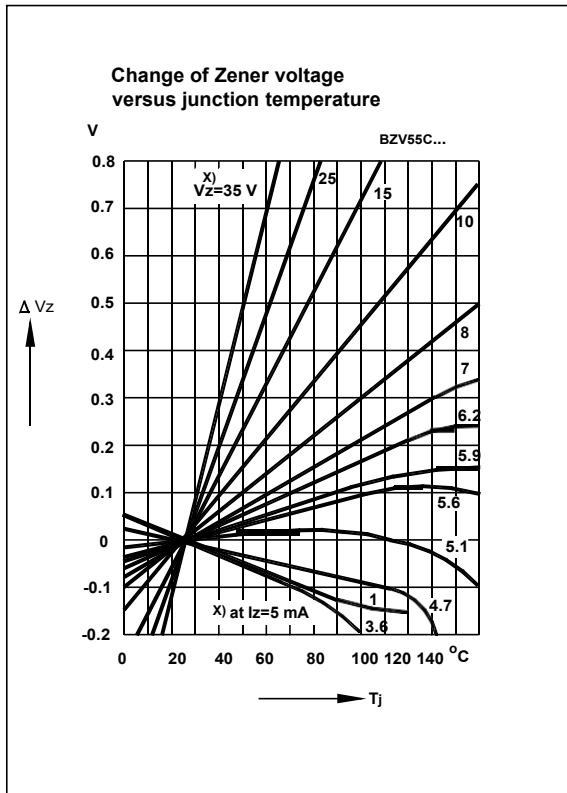
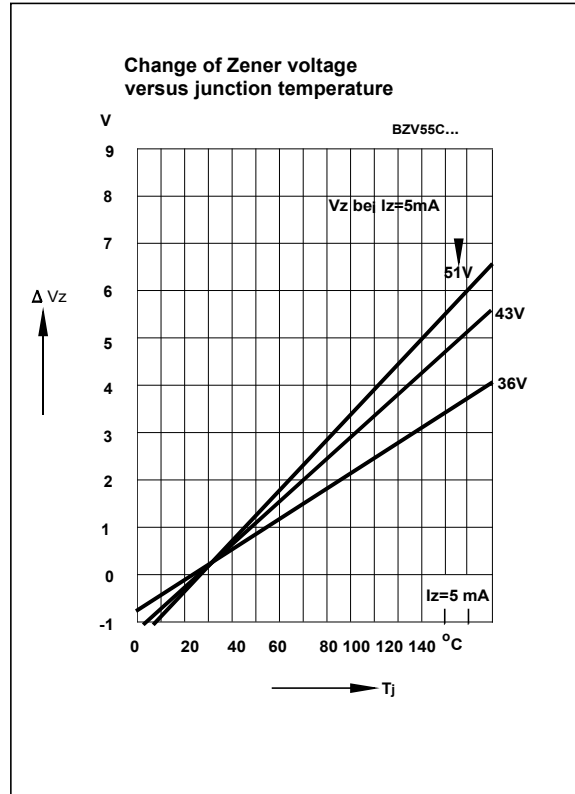
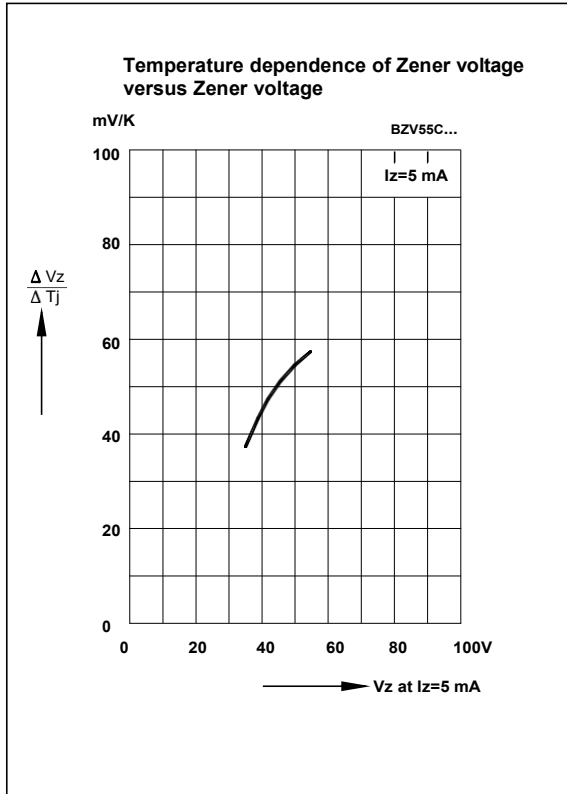


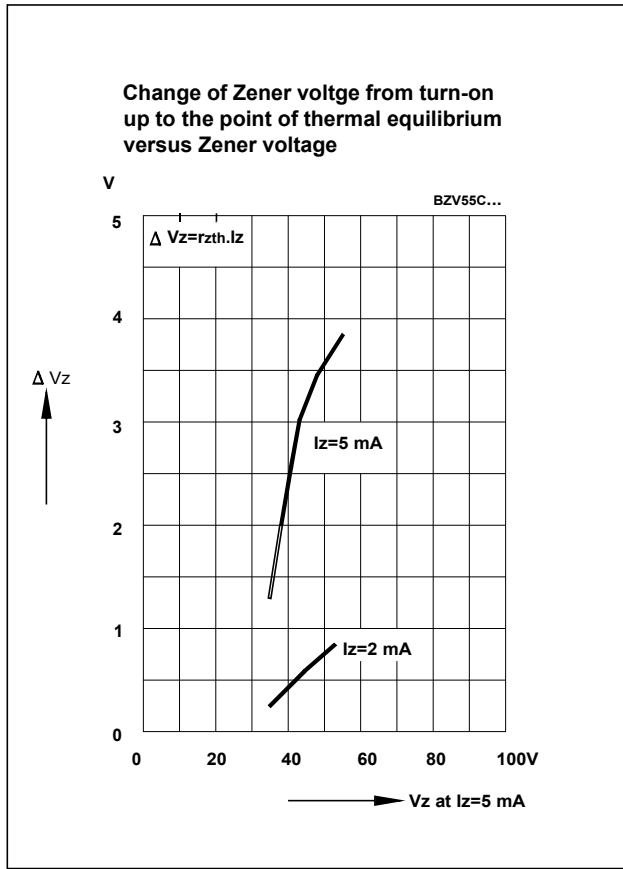
Breakdown characteristics
T_j = constant (pulsed)











Attention

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- MSKSEMI Semiconductor strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringement of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor product that you intend to use.

Attention

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- MSKSEMI Semiconductor strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringement of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor product that you intend to use.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Zener Diodes](#) category:

Click to view products by [MSKSEMI](#) manufacturer:

Other Similar products are found below :

[RKZ13B2KG#P1](#) [DL5234B](#) [1N4682](#) [1N4693](#) [1N4732A](#) [1N4736A](#) [1N4750A](#) [1N4759ARL](#) [1N5241B](#) [1N5365B](#) [1N5369B](#) [1N747A](#)
[1N964B](#) [1N966B](#) [1N968B](#) [1N972B](#) [JANS1N4974US](#) [1N4692](#) [1N4702](#) [1N4704](#) [1N4711](#) [1N4714](#) [1N4745ARL](#) [1N4752ARL](#) [1N4760ARL](#)
[1N5221B](#) [1N5242BTR](#) [1N5350B](#) [1N5352B](#) [1N961BRR1](#) [1N964BRL](#) [RKZ5.1BKU#P6](#) [3SMAJ5946B-TP](#) [3SMAJ5950B-TP](#)
[MMSZ5230BQ-13-F](#) [MMSZ5232BQ-13-F](#) [BZX84C7V5](#) [3SMAJ5945B-TP](#) [3SMAJ5947B-TP](#) [3SMBJ5941B-TP](#) [DZ2S240M0L](#) [SMAZ27-](#)
[TP](#) [ZMM5224B-7](#) [RD16UM-T1-A](#) [RD39S-T1-A](#) [RD10S-T1-A](#) [CDZT2R5.6B](#) [1N4762A G](#) [Z1SMA18](#) [JANTX1N4553B](#)